TOSHIBA INSULATED GATE BIPOLAR TRANSISTOR SILICON N-CHANNEL IGBT

GT8Q101

HIGH POWER SWITCHING APPLICATIONS

MOTOR CONTROL APPLICATIONS

• High Input Impedance

• High Speed : $t_f = 0.5 \mu s$ (Max.)

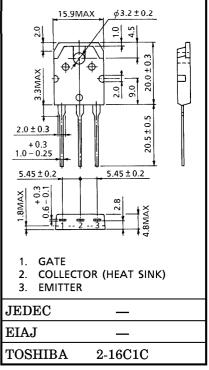
• Low Saturation Voltage: VCE (sat)=4.0V (Max.)

• Enhancement-Mode

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERIS	SYMBOL	RATING	UNIT		
Collector-Emitter Voltage		v_{CES}	1200	V	
Gate-Emitter Voltage	V_{GES}	±20	V		
Collector Current	DC	$I_{\mathbf{C}}$	8	A	
	1ms	I_{CP}	16		
Collector Power Dissipat (Tc=25°C)	PC	100	w		
Junction Temperature	T_{j}	150	°C		
Storage Temperature Range		$\mathrm{T_{stg}}$	-55~150	°C	

Unit in mm

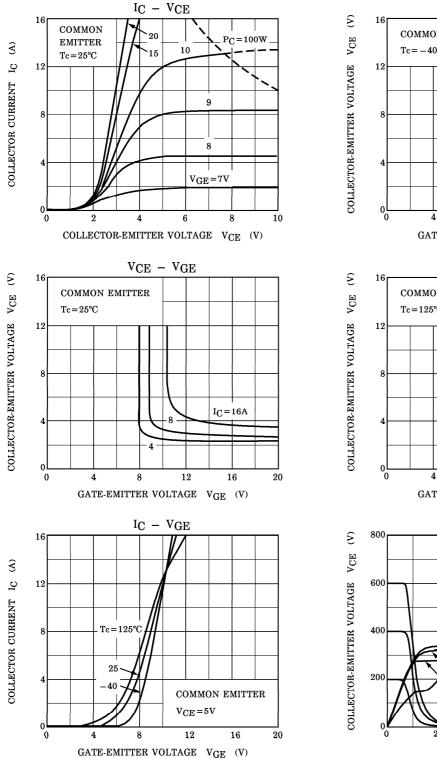


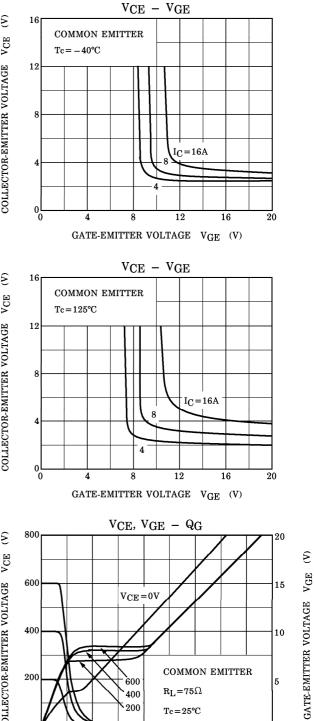
Weight: 4.6g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT		
Gate Leakage Current		IGES	$V_{GE} = \pm 20V, V_{CE} = 0$			±500	nA		
Collector Cut-off Current		I_{CES}	$V_{CE} = 1200V, V_{GE} = 0$	_	_	1.0	mA		
Gate-Emitter	Cut-off Voltage	V _{GE} (OFF)	$I_{C}=8mA$, $V_{CE}=5V$	3.0	_	6.0	V		
Collector-Emitter Saturation Voltage		V _{CE} (sat)	$I_{C}=8A, V_{GE}=15V$	_	3.0	4.0	V		
Input Capacitance		$c_{ m ies}$	$V_{CE} = 10V, V_{GE} = 0, f = 1MHz$	_	1100	_	pF		
Switching Time	Rise Time	t_r	$\begin{array}{c c} V_{OUT} \\ V_{IN} \\ 150\Omega \end{array}$	_	0.3	0.6			
	Turn-on Time	ton		_	0.4	0.8	μ s		
	Fall Time	t_f		_	0.3	0.5			
	Turn-off Time	$t_{ m off}$		_	0.8	1.5			

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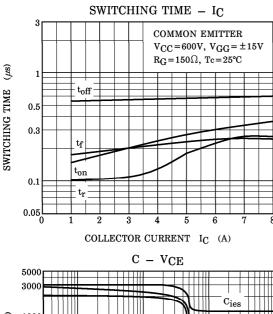
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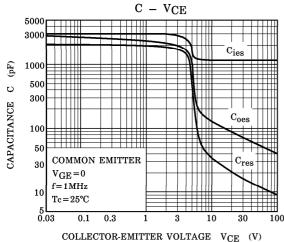
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GATE CHARGE QG (nC)

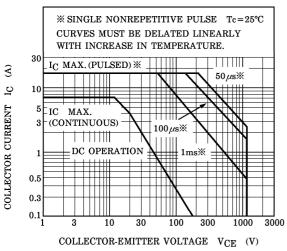
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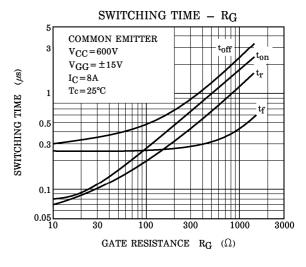
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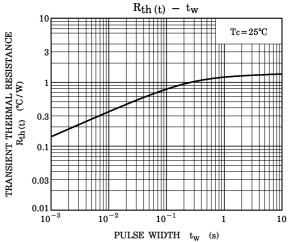


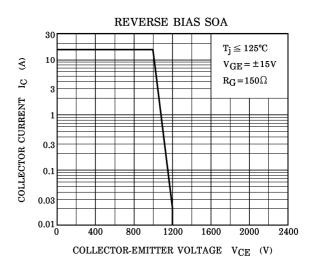


SAFE OPERATING AREA









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